Silicon NPN transistor in a TO-92 Plastic Package.

/ Absolute Maximum Ratings(Ta=25)

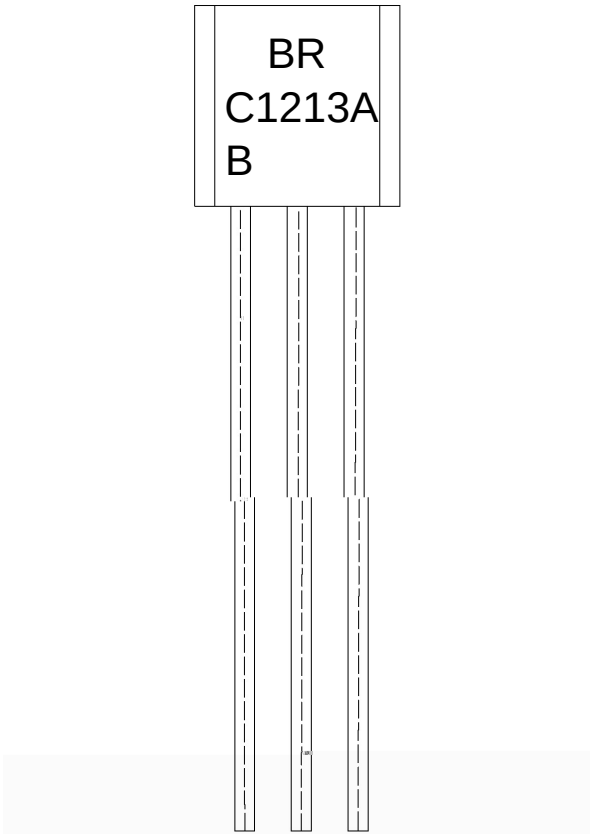
Parameter	Symbol		Rating	Unit
Collector to Base Voltage	V_{CBO}	2SC1213	35	V
		2SC1213A	50	
Collector to Emitter Voltage	V_{CEO}	2SC1213	35	V
		2SC1213A	50	
Emitter to Base Voltage	V_{EBO}		4.0	V
Collector Current - Continuous	I_C		500	mA
Collector Power Dissipation	P_C		400	mW
Junction Temperature	T_j		150	
Storage Temperature Range	T_{stg}		-55 150	

/ Electrical Characteristics(Ta=25)

Parameter	Symbol		Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	2SC1213	I_C=10μA I_C=1.0mA	35			V
		2SC1213A		50			
Collector to Emitter Breakdown Voltage	V_{CEO}	2SC1213	I_C=1.0mA I_B=0	35			V
		2SC1213A		50			
Emitter to Base Breakdown Voltage	V_{EBO}		I_E=10μA I_C=0	4.0			V
Collector Cut-Off Current	I_{CBO}		V_{CB}=20V I_E=0			0.5	μA
DC Current Gain	$h_{FE(1)}$		V_{CE}=3.0V I_C=10mA	60		320	
	$h_{FE(2)}$		V_{CE}=3.0V I_C=500mA	10			
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$		I_C=150mA I_B=15mA		0.2	0.6	V
Base to Emitter Voltage	V_{BE}		V_{CE}=3.0V I_C=10mA		0.64		V

/ Package Dimensions

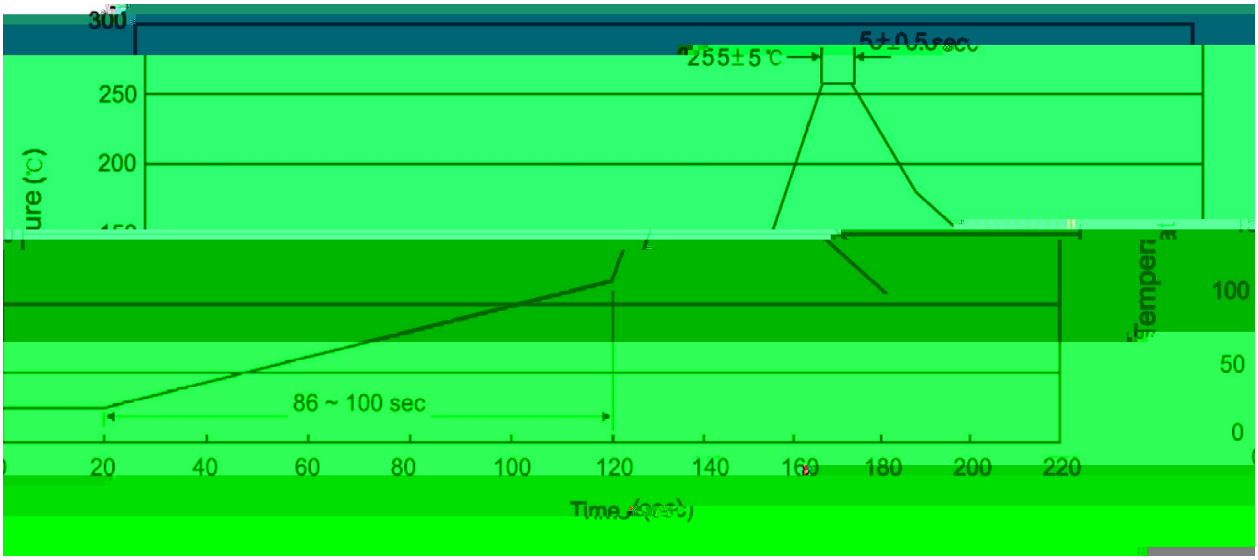
/ Marking Instructions



Note:

BR:	Company Code.
C1213A:	Product Type.
B:	h_{FE} Classifications Symbol
****:	Lot No. Code,code change with Lot No.

( ) / Temperature Profile for Dip Soldering(Pb-Free)



1	25	150	60	90sec;	
2	255	5	5	0.5sec;	
3		2	10	/sec.	

Note:
1.Preheating:25~150 , Time:60~90sec.
2.Peak Temp.:255 5 , Duration:5 0.5sec.
3. Cooling Speed: 2~10 /sec.

/ Resistance to Soldering Heat Test Conditions

270 5 10 1 sec. Temp:270±5 Time:10±1 sec

/ Packaging SPEC.

/ BULK

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm3)		
	只袋	袋盒	只盒	盒箱	只箱	袋	盒	箱

/ AMMO

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm3)	
	只纸带	纸带盒	纸带层盒	盒箱	只箱	盒	箱
							小箱 , 大箱

/ Notices